Icemos Technology Ltd Product Specification 1003.290701 Issue Date 30 October 2014 11:0

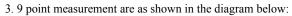
Part Number (7
Part Number (Customer

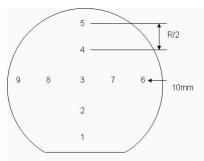
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	4.0	Growth Method	CZ	Wafer Vendor
	5.0	Туре	Any	Wafer Vendor
	6.0	Dopant	Any	Wafer Vendor
	7.0	Resistivity	0.1~ 100 ohm cm	Wafer Vendor
	8.0	Overall Thickness	500.00 +/- 10.00 um	Wafer Vendor
	9.0	Total Thickness Variation (TTV)	<3.00um	Guaranteed by process
	10.0	Bow	<50.00um	ADE to ASTM F534, 20%
	11.0	Warp	<50.00um	ADE to ASTM F657, 20%
	12.0	Lasermarking	On wafer FRONTSIDE opposite the flat as per attachment. Scribe format: [ICE-6-500.XXXX] (unique scribe)	Guaranteed by process
	13.0	Orientation	<100> +/-0.5	Wafer Vendor
	14.0	Back Surface Quality	Polished with light handling marks.	Wafer Vendor
	15.0	Front Surface Quality	Prime polished	Wafer Vendor
	16.0	Edge Chips	None	Bright Light 100% (note 2)
HandleSilicon	17.0	Handle Thickness	500.00 +/- 10.00 um	ADE
	18.0	Surface Haze	None	Bright Light, 100% (note 2).
	19.0	Total scratch length	None	Bright Light, 100% (note 2).

Page 1 of 2 10/12/2019 www.icemostech.com

Part Number		Customer	
Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box:	Max 25	
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspec	tion performed using microscope scan as below. 5x objective.	
		pections performed exclude all wafer area outside the edge exclusion	on defined in Overall

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information